

ZXMN10A07F

100V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 100V$; $R_{DS(ON)} = 1\Omega$ $I_D = 0.64A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

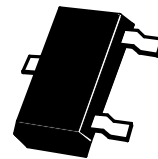
- DC - DC Converters
- Power Management Functions
- Relay and Solenoid driving
- Motor control

ORDERING INFORMATION

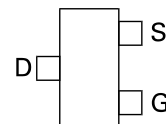
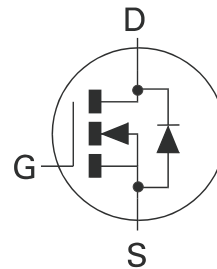
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN10A07FTA	7"	8mm	3000 units
ZXMN10A07FTC	13"	8mm	10000 units

DEVICE MARKING

- 7N1



SOT23



Top View

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ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	100	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^{\circ}C$ (b) $V_{GS}=10V$; $T_A=70^{\circ}C$ (b) $V_{GS}=10V$; $T_A=25^{\circ}C$ (a)	I_D	0.64 0.51 0.56	A
Pulsed Drain Current (c)	I_{DM}	2.5	A
Continuous Source Current (Body Diode) (b)	I_S	2	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	2.5	A
Power Dissipation at $T_A=25^{\circ}C$ (a) Linear Derating Factor	P_D	625 5	mW mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b) Linear Derating Factor	P_D	806 6.4	mW mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^{\circ}C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	$^{\circ}C/W$
Junction to Ambient (b)	$R_{\theta JA}$	155	$^{\circ}C/W$

NOTES

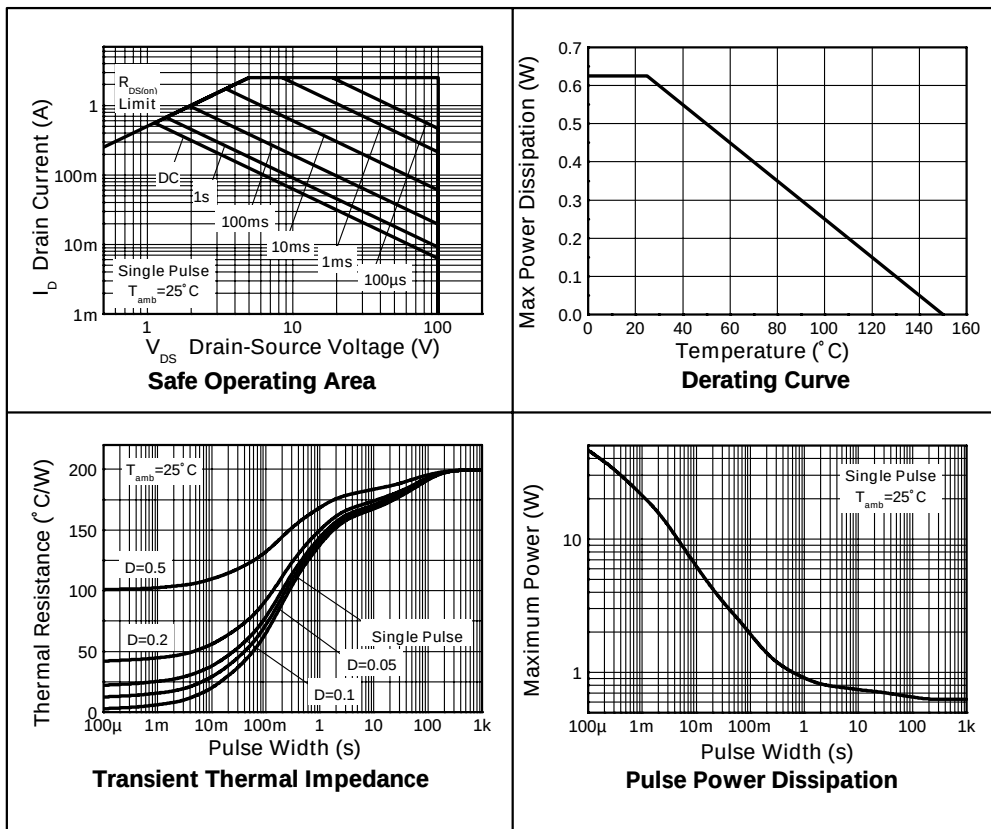
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.05$, pluse width 10 μ S - pulse width limited by maximum junction temperature.

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THERMAL CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

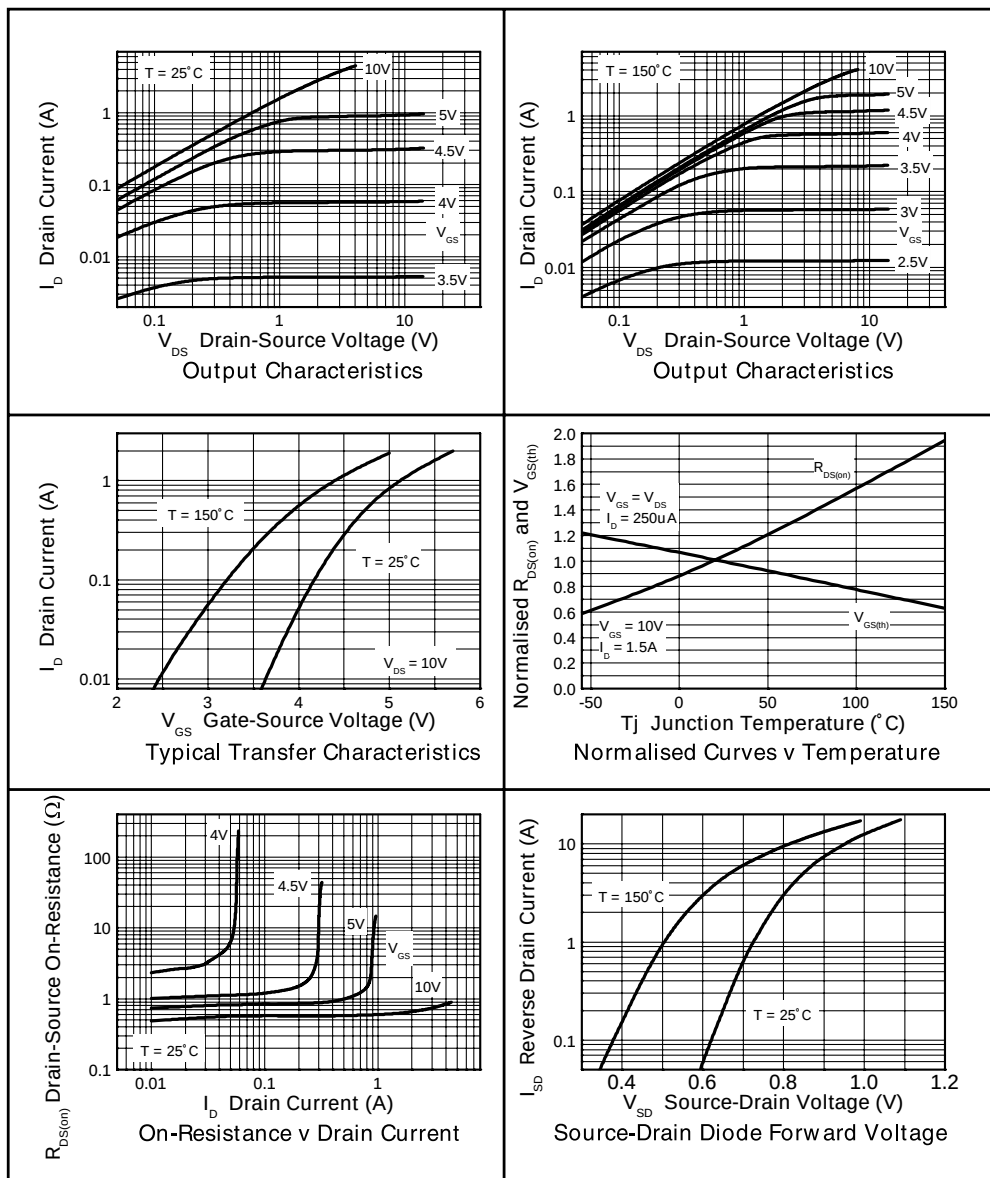
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	100			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =60V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	2.0		4.0	V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			1 1.1	Ω Ω	V _{GS} =10V, I _D =1.5A V _{GS} =6V, I _D =1A
Forward Transconductance (3)	g _{fs}		1.6		S	V _{DS} =15V, I _D =1A
DYNAMIC (3)						
Input Capacitance	C _{iss}		138		pF	V _{DS} =60 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		12		pF	
Reverse Transfer Capacitance	C _{rss}		6		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		1.8		ns	V _{DD} =50V, I _D =1A R _G =6.0Ω, V _{GS} =10V
Rise Time	t _r		1.5		ns	
Turn-Off Delay Time	t _{d(off)}		4.1		ns	
Fall Time	t _f		2.1		ns	
Total Gate Charge	Q _g		2.9		nC	V _{DS} =50V, V _{GS} =10V, I _D =1.8A
Gate-Source Charge	Q _{gs}		0.7		nC	
Gate-Drain Charge	Q _{gd}		1		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			0.95	V	T _J =25°C, I _S =1.5A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		27		ns	T _J =25°C, I _F =1.8A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		12		nC	

NOTES

- (1) Measured under pulsed conditions. Width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.

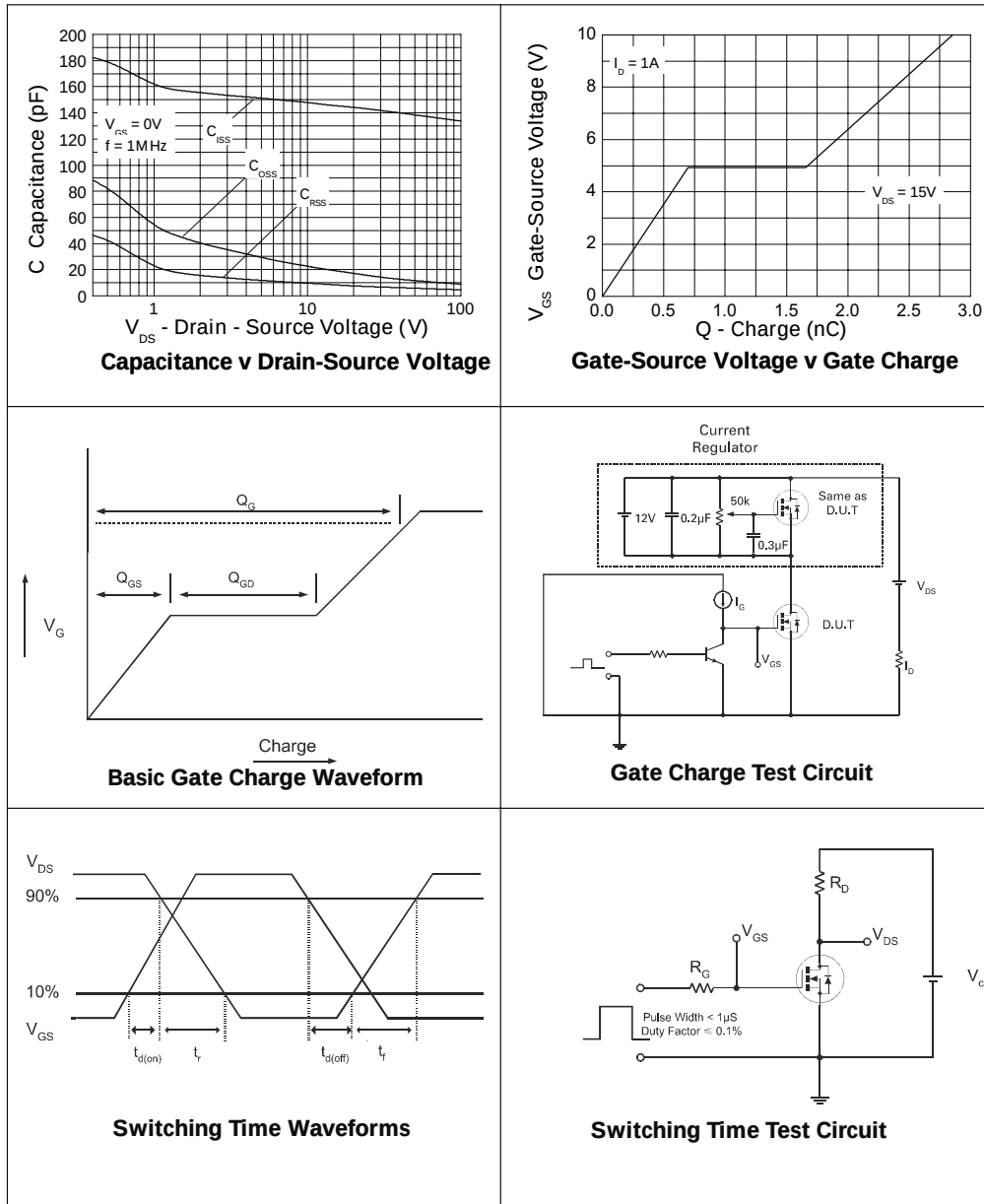
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TYPICAL CHARACTERISTICS



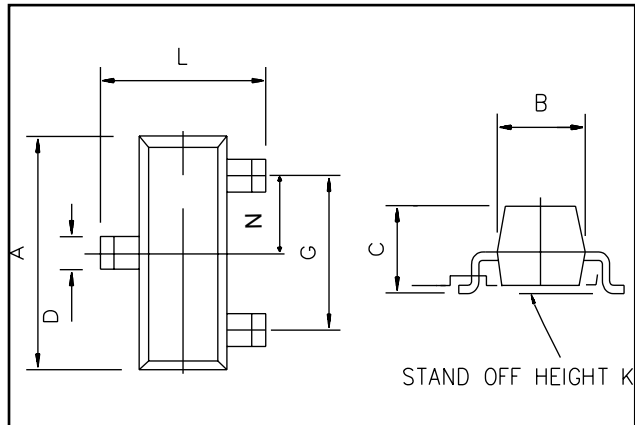
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TYPICAL CHARACTERISTICS

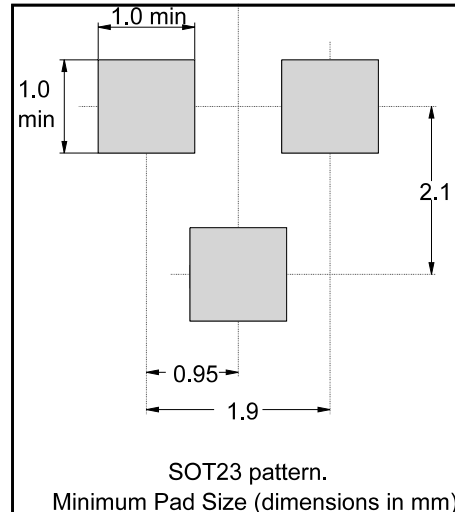


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PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



PAD LAYOUT DETAILS

DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	2.67	3.05	0.105	0.120
B	1.20	1.40	0.047	0.055
C	—	1.10	—	0.043
D	0.37	0.53	0.0145	0.021
F	0.085	0.15	0.0033	0.0059
G	NOM 1.9		NOM 0.075	
K	0.01	0.10	0.0004	0.004
L	2.10	2.50	0.0825	0.0985
N	NOM 0.95		NOM 0.037	

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PROVISIONAL ISSUE B - AUGUST 2001